

2-Input AND Gate with Open Drain Output

NLV74VHC1G09

The NLV74VHC1G09 is an advanced high speed CMOS 2-input AND gate with open drain output fabricated with silicon gate CMOS technology. It achieves high speed operation similar to equivalent Bipolar Schottky TTL while maintaining CMOS low power dissipation.

The input structures provide protection when voltages up to 5.5 V are applied, regardless of the supply voltage. This allows the device to be used to interface 5 V circuits to 3 V circuits. Some output structures also provide protection when V_{CC} = 0 V and when the output voltage exceeds $V_{CC}.$ These input and output structures help prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

Features

- Designed for 2.0 V to 5.5 V V_{CC} Operation
- 4.3 ns t_{PD} at 5 V (typ)
- Inputs/Outputs Over-Voltage Tolerant up to 5.5 V
- I_{OFF} Supports Partial Power Down Protection
- Source/Sink 8 mA at 3.0 V
- Available in SC-88A and TSOP-5 Packages
- Chip Complexity < 100 FETs
- NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

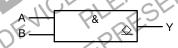


Figure 1 Logic Symbol

MARKING DIAGRAMS



SC-88A DF SUFFIX CASE 419A





TSOP-5 DT SUFFIX CASE 483





XX M = Specific Device Code

1 = Date Code*

= Pb-Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or position may vary depending upon manufacturing location.

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 6 of this data sheet.

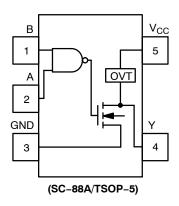


Figure 2. Pinout (Top View)

PIN ASSIGNMENT

(SC-88A/TSOP-5)

Pin	Function
1	В
2	А
3	GND
4	Y
5	V _{CC}

FUNCTION TABLE

	Pin	Function	Input	Output
	1	В	A B	Y
	2	Α	L	FID
	3	GND	A H	I. I.
	4	Υ	H L	L
	5	V _{CC}	H CH	Z
THIS DI	SIS IS	O RECONS	H LP H PH	MATIC

MAXIMUM RATINGS

Symbol	С	haracteristics	Value	Unit
V _{CC}	DC Supply Voltage		-0.5 to +7.0	V
V _{IN}	DC Input Voltage		-0.5 to +7.0	V
V _{OUT}	DC Output Voltage	1Gxx	-0.5 to V _{CC} + 0.5	V
		1GTxx Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	-0.5 to V _{CC} + 0.5 -0.5 to +7.0 -0.5 to +7.0	
I _{IK}	DC Input Diode Current	V _{IN} < GND	-20	mA
lok	DC Output Diode Current	1Gxx V _{OUT} > V _{CC} , V _{OUT} < GND	±20	mA
		1GTxx V _{OUT} < GND	-20	
I _{OUT}	DC Output Source/Sink Current	±25	mA	
I _{CC} or I _{GND}	DC Supply Current per Supply Pir	±50	mA	
T _{STG}	Storage Temperature Range		-65 to +150	7 ∘C
TL	Lead Temperature, 1 mm from Ca	se for 10 secs	260	°C
TJ	Junction Temperature Under Bias		+150	°C
$\theta_{\sf JA}$	Thermal Resistance (Note 2)	SC-88A	377	°C/W
P_{D}	Power Dissipation in Still Air	SC-88A	332	mW
MSL	Moisture Sensitivity		Level 1	_
F _R	Flammability Rating	Oxygen Index: 28 to 34	UL 94 V-0 @ 0.125 in	_
V _{ESD}	ESD Withstand Voltage (Note 3)	Human Body Model Charged Device Model	2000 1000	V
I _{Latchup}	Latchup Performance (Note 4)	WE, OO, C	±100	mA

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- Applicable to devices with outputs that may be tri-stated.
 Measured with minimum pad spacing on an FR4 board, using 10mm-by-1inch, 2 ounce copper trace no air flow per JESD51-7.
 HBM tested to ANSI/ESDA/JEDEC JS-001-2017. CDM tested to EIA/JESD22-C101-F. JEDEC recommends that ESD qualification to EIA/JESD22-A115-A (Machine Model) be discontinued per JEDEC/JEP172A.
 Tested to EIA/JESD78 Class II.

RECOMMENDED OPERATING CONDITIONS

Symbol		haracteristics	Min	Max	Unit
V_{CC}	Positive DC Supply Voltage	Positive DC Supply Voltage			
V_{IN}	DC Input Voltage		0	5.5	V
V _{OUT}	DC Output Voltage	1Gxx	0	V_{CC}	V
		1GTxx Active–Mode (High or Low State) Tri–State Mode (Note 1) Power–Down Mode (V _{CC} = 0 V)	0 0 0	V _{CC} 5.5 5.5	
T _A	Operating Temperature Range		-55	+125	°C
t _r , t _f	Input Rise and Fall Time	V _{CC} = 3.0 V to 3.6 V V _{CC} = 4.5 V to 5.5 V	0 0	100 20	ns/V

Functional operation above the stresses listed in the Recommended Operating Ranges is not implied. Extended exposure to stresses beyond the Recommended Operating Ranges limits may affect device reliability.

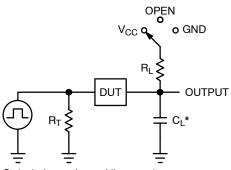
DC ELECTRICAL CHARACTERISTICS (MC74VHC1G09)

		Test	V _{CC}	1	_A = 25°	С	-40°C ≤ 7	Γ _A ≤ 85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Conditions	(V)	Min	Тур	Max	Min	Max	Min	Max	Uni
V _{IH}	High-Level Input		2.0	1.5	-	-	1.5	_	1.5	-	٧
	Voltage		3.0	2.1	-	-	2.1	-	2.1	-	1
			4.5	3.15	-	-	3.15	-	3.15	-	
			5.5	3.85	-	-	3.85	-	3.85	-	
V _{IL}	Low-Level Input		2.0	_	-	0.5	-	0.5	-	0.5	V
	Voltage		3.0	-	-	0.9	-	0.9	-	0.9	
			4.5	-	-	1.35	-	1.35	-	1.35	
			5.5	-	-	1.65	-	1.65	-	1.65	
V _{OL}	Low-Level Output Voltage	$\begin{aligned} &V_{IN} = V_{IH} \text{ or } V_{IL} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 50 \mu\text{A} \\ &I_{OL} = 4 m\text{A} \\ &I_{OL} = 8 m\text{A} \end{aligned}$	2.0 3.0 4.5 3.0 4.5	- - - -	0.0 0.0 0.0 - -	0.1 0.1 0.1 0.36 0.36	- - - -	0.1 0.1 0.1 0.44 0.44	- - - - - - -	0.1 0.1 0.1 0.52 0.52	V
I _{IN}	Input Leakage Current	V _{IN} = 5.5 V or GND	2.0 to 5.5	-	-	±0.1	-	±1.0	NA	±1.0	μΑ
I _{OZ}	3-State Output Leakage Current	V _{OUT} = 0 V to 5.5 V	5.5	-	Ī	±0.25		±2.5	-	± 2.5	μΑ
I _{OFF}	Power Off Leakage Current	V _{IN} = 5.5 V	0.0		-	1.0	:O-P	510	104	10	μΑ
I _{CC}	Quiescent Supply Current	V _{IN} = V _{CC} or GND	5.5	-		1.0	IRO	20	_	40	μΑ
AC ELEC	CTRICAL CHARACT	TERISTICS		000	W	10	MFC)`			

			- C.	J T	A = 25°	c	-40°C ≤ 1	Γ _A ≤ 85°C	-55°C ≤ T	_A ≤ 125°C	
Symbol	Parameter	Conditions	V _{CC} (V)	Min	Тур	Max	Min	Max	Min	Max	Unit
t _{PZL}	Propagation Delay,	$C_L = 15 pF$	3.0 to 3.6). -\	6.2	8.8	-	10.5	-	12.5	ns
	(A or B) to Y (Figures 3 and 4)	C _L = 50 pF	CVX	12	8.7	12.3	-	14.0	-	16.5	
		C _L = 15 pF	4.5 to 5.5	_	4.3	5.9	-	7.0	-	9.0	
		C _L = 50 pF	,SV.	_	5.8	7.9	-	9.0	-	11.0	
t _{PLZ}	Propagation Delay,	C _L = 15 pF	3.0 to 3.6	_	6.5	9.7	-	11.5	-	14.5	ns
	(A or B) to Y (Figures 3 and 4)	$C_{L} = 50 \text{ pF}$		_	8.7	12.3	-	14.0	-	16.5	
<	His	C _L = 15 pF	4.5 to 5.5	_	4.8	6.8	-	8.0	-	10.0	
		C _L = 50 pF		_	5.8	7.9	-	9.0	-	11.0	
C _{IN}	Input Capacitance			-	4.0	10	-	10	-	10	pF
C _{OUT}	Output Capacitance	Output in High Impedance State		-	6.0	ı	l	-	-	Ι	pF

		Typical @ 25°C, V _{CC} = 5.0 V	
C _{PD}	Power Dissipation Capacitance (Note 5)	8.0	pF

^{5.} C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load. Average operating current can be obtained by the equation: I_{CC(OPR)} = C_{PD} • V_{CC} • f_{in} + I_{CC}. C_{PD} is used to determine the no–load dynamic power consumption; P_D = C_{PD} • V_{CC}² • f_{in} + I_{CC} • V_{CC}.



Test	Switch Position	C _L , pF	R_L, Ω
t _{PLH} / t _{PHL}	Open	See AC Characteristics Table	Х
t _{PLZ} / t _{PZL}	V _{CC}		1 k
t _{PHZ} / t _{PZH}	GND		1 k

X = Don't Care

 C_L includes probe and jig capacitance R_T is Z_{OUT} of pulse generator (typically 50 $\Omega)$ f = 1 MHz

Figure 3. Test Circuit

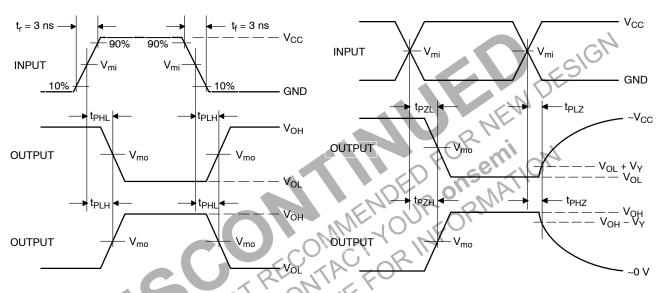


Figure 4. Switching Waveforms

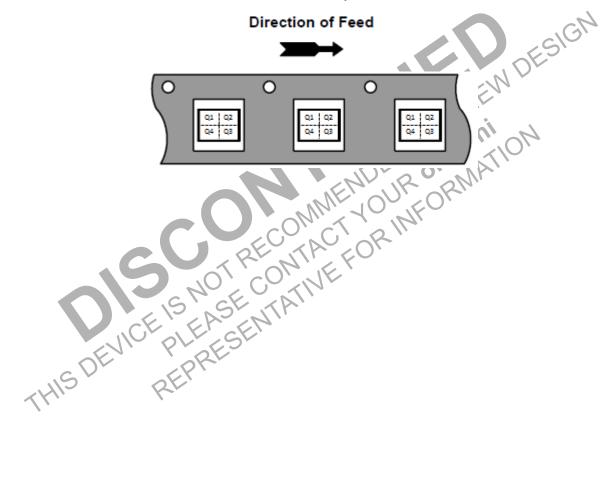
	INCHAIR CE	V _{mo}	, V	
V _{CC} , V	V _{mi} , V	t _{PLH} , t _{PHL}	t_{PZL} , t_{PLZ} , t_{PZH} , t_{PHZ}	V _Y , V
3.0 to 3.6	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3
4.5 to 5.5	V _{CC} /2	V _{CC} /2	V _{CC} /2	0.3

ORDERING INFORMATION

Device	Packages	Specific Device Code	Pin 1 Orientation (See below)	Shipping [†]
NLVVHC1G09DFT1G*	SC-88A	VX	Q2	3000 / Tape & Reel
NLVVHC1G09DFT2G*	SC-88A	VX	Q4	3000 / Tape & Reel
MC74VHC1G09DFT2G-L22038	SC-88A	VX	Q4	3000 / Tape & Reel
MC74VHC1G09DTT1G	TSOP-5	VX	Q4	3000 / Tape & Reel
NLV74VHC1G09DTT1G*	TSOP-5	VX	Q4	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Pin 1 Orientation in Tape and Reel



^{*} NLV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable.





SC-88A (SC-70-5/SOT-353) CASE 419A-02 ISSUE M

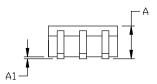
DATE 11 APR 2023

NOTES:

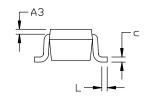
- 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
- CONTROLLING DIMENSION: MILLIMETERS
- 419A-01 DBSDLETE. NEW STANDARD 419A-02
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.1016MM PER SIDE.

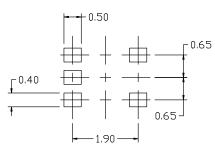
DIM	MI	MILLIMETERS				
ויודת	MIN.	N□M.	MAX.			
А	0.80	0.95	1.10			
A1			0.10			
A3	0.20 REF					
b	0.10	0.20	0.30			
C	0.10		0.25			
D	1.80	2.00	2,20			
Е	2.00	2.10	2.20			
E1	1.15	1.25	1.35			
е	0.65 BSC					
L	0.10	0.15	0.30			

е Ε1 0 5X b



◆ 0.2 M B M





RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

XXX = Specific Device Code

= Date Code

= Pb-Free Package

(Note: Microdot may be in either location)

STYLE 1:
PIN 1. BASE
EMITTER
3. BASE
COLLECTOR
COLLECTOR

3. EMITTER 1

4. COLLECTOR

STYLE 2: PIN 1. ANODE 2. EMITTER 3. BASE 4. COLLECTOR CATHODE

3. BASE

4. COLLECTOR

STYLE 3: PIN 1. ANODE 1 2. N/C 3. ANODE 2 4. CATHODE 2 5. CATHODE 1

4. BASE

5. EMITTER

STYLE 4: PIN 1. SOURCE 1 2. DRAIN 1/2 3 SOURCE 1 4. GATE 1 5. GATE 2

3. ANODE 4. ANODE

ANODE
 ANODE

STYLE 5: PIN 1. CATHODE 2. COMMON ANODE 3. CATHODE 2 4. CATHODE 3 5. CATHODE 4

out in the datasheet refer to the device

datasheet pinout or pin assignment.

STYLE 6: STYLE 7: STYLE 8: STYLE 9: Note: Please refer to datasheet for PIN 1. EMITTER 2 PIN 1. CATHODE 2. COLLECTOR 3. N/C PIN 1. ANODE 2. CATHODE PIN 1. BASE style callout. If style type is not called 2. EMITTER 2. BASE 2

5. COLLECTOR 2/BASE 1 5. COLLECTOR **DOCUMENT NUMBER:** 98ASB42984B

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DESCRIPTION: SC-88A (SC-70-5/SOT-353) PAGE 1 OF 1

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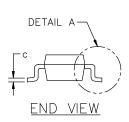


TSOP-5 3.00x1.50x0.95, 0.95P **CASE 483 ISSUE P**

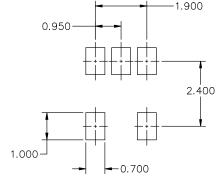
DATE 01 APR 2024

NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME 1. Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS (ANGLES IN DEGREES). MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OF GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSION D.
- OPTIONAL CONSTRUCTION: AN ADDITIONAL TRIMMED LEAD IS ALLOWED IN THIS LOCATION. TRIMMED LEAD NOT TO EXTEND MORE THAN 0.2 FROM BODY.



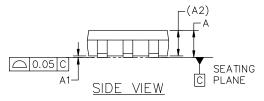
DIM	MILLIMETERS		
	MIN.	NOM.	MAX.
А	0.900	1.000	1.100
A1	0.010	0.055	0.100
A2	0.950 REF.		
b	0.250	0.375	0.500
С	0.100	0.180	0.260
D	2.850	3.000	3.150
Е	2.500	2.750	3.000
E1	1.350	1.500	1.650
е	0.950 BSC		
L	0.200	0.400	0.600
Θ	0.	5°	10°

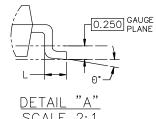


RECOMMENDED MOUNTING FOOTPRINT*

FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

NOTE 5 В Ė1 PIN 1 **IDENTIFIER** A TOP VIEW





SCALE 2:1

GENERIC MARKING DIAGRAM*





Discrete/Logic

XXX = Specific Device Code

XXX = Specific Device Code М = Date Code

= Assembly Location = Year

= Pb-Free Package

W = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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DESCRIPTION: TSOP-5 3.00x1.50x0.95, 0.95P **PAGE 1 OF 1**

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